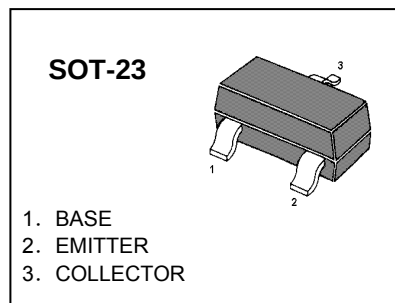


TRANSISTOR (NPN)

FEATURES

Epitaxial planar die construction

Complementary PNP Type available(MMBT2907A)



MARKING: 1P

MAXIMUM RATINGS (T_a=25°C unless otherwise noted)

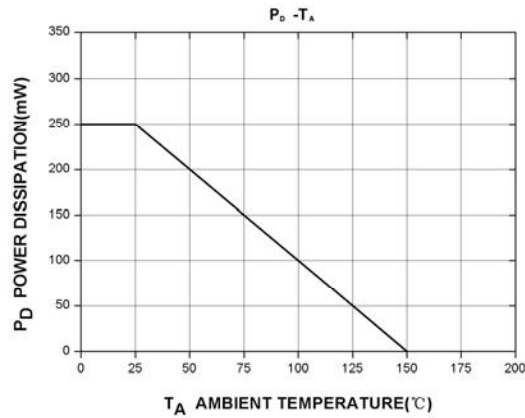
Symbol	Parameter	Value	Units
V _{CBO}	Collector-Base Voltage	75	V
V _{CEO}	Collector-Emitter Voltage	40	V
V _{EBO}	Emitter-Base Voltage	6	V
I _C	Collector Current -Continuous	600	mA
P _C	Collector Dissipation	250	mW
R _{θJA}	Thermal Resistance, Junction to Ambient	500	°C/W
T _J	Junction Temperature	150	°C
T _{stg}	Storage Temperature	-55to+150	°C

ELECTRICAL CHARACTERISTICS (T_a=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C = 10μA, I _E =0	75			V
Collector-emitter breakdown voltage	V _{(BR)CEO} *	I _C = 10mA, I _B =0	40			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =10μA, I _C =0	6			V
Collector cut-off current	I _{CBO}	V _{CB} =60V, I _E =0			0.01	μA
Collector cut-off current	I _{CEX}	V _{CE} =30V, V _{BE(off)} =3V			0.01	μA
Emitter cut-off current	I _{EBO}	V _{EB} = 3V, I _C =0			0.1	μA
DC current gain	h _{FE(1)} *	V _{CE} =10V, I _C = 150mA	100		300	
	h _{FE(2)}	V _{CE} =10V, I _C = 0.1mA	40			
	h _{FE(3)} *	V _{CE} =10V, I _C = 500mA	42			
Collector-emitter saturation voltage	V _{CE(sat)} *	I _C =500 mA, I _B = 50mA I _C =150 mA, I _B =15mA			1 0.3	V
Base-emitter saturation voltage	V _{BE(sat)} *	I _C =500 mA, I _B = 50mA I _C =150 mA, I _B =15mA			2.0 1.2	V
Transition frequency	f _T	V _{CE} =20V, I _C = 20mA, f=100MHz	300			MHz
Delay time	t _d	V _{CC} =30V, V _{BE(off)} =-0.5V I _C =150mA, I _{B1} = 15mA			10	nS
Rise time	t _r				25	nS
Storage time	t _s	V _{CC} =30V, I _C =150mA I _{B1} =-I _{B2} =15mA			225	nS
Fall time	t _f				60	nS

*pulse test: Pulse Width ≤300μs, Duty Cycles ≤ 2.0%.

Typical Characteristics



MMBT2222A

